



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Title: SILICON CARBIDE GATE TRANSISTOR AND FABRICATION PROCESS

Docket No.: 303.326US1

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Examiner:

Group Art Unit: 2812

Assistant Commissioner for Patents
Washington, D.C. 20231

We are transmitting herewith the following attached items (as indicated with an "X"):

- ☒ A return postcard.
- ☒ A Supplemental Information Disclosure Statement (1 pgs.), Form 1449 (1 pgs.), and copies of 12 cited references.

Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional required fees or credit overpayment to Deposit Account No. 19-0743.

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this Transmittal Letter and the paper, as described above, are being deposited in the United States Postal Service, as first class mail, in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on this 6 day of January, 1999.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938, Minneapolis, MN 55402 (612-373-6900)

By: Daniel J. Kluth
Atty. Daniel J. Kluth
Reg. No. 32,146

(GENERAL)

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